Power on Silicon with on-die Magnetics:

The start of a Revolution in Power Delivery and Power Management for SoC's and High Performance Applications

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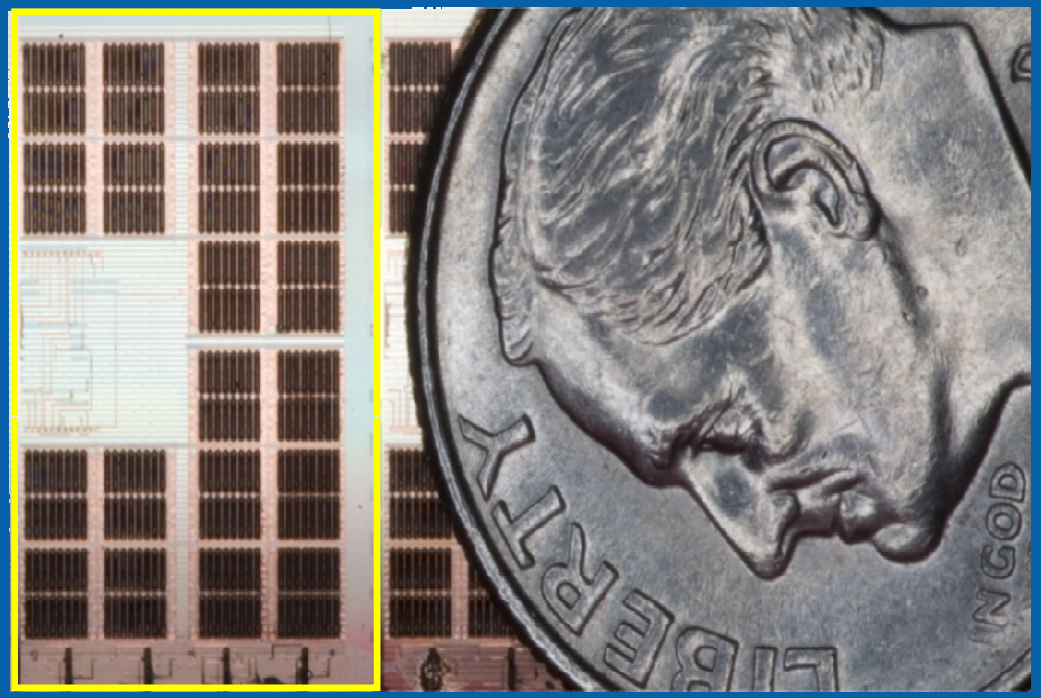
Agenda

- Introduction
- The Revolutions Starts…
  - Architecture, magnetics/circuits, results
- Summary

From High Performance Servers to Small CE devices the trend in platform power needs to shrink, become more efficient, and be more cost effective.

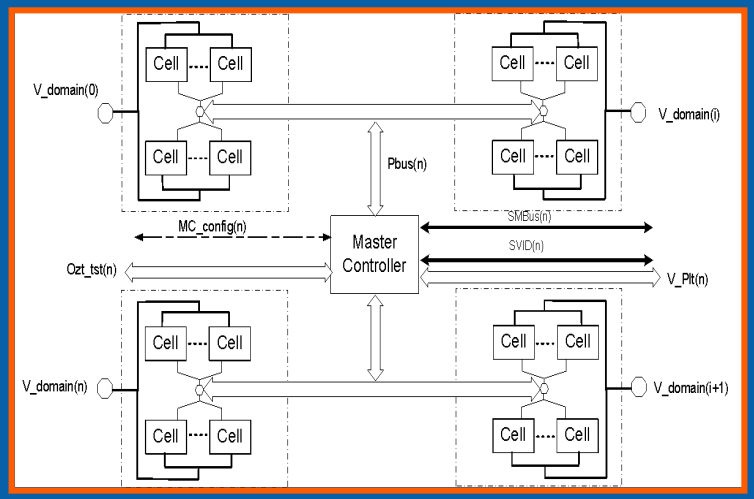
Overview of ISVR

- Architecture
- Magnetics/Circuits
- Results

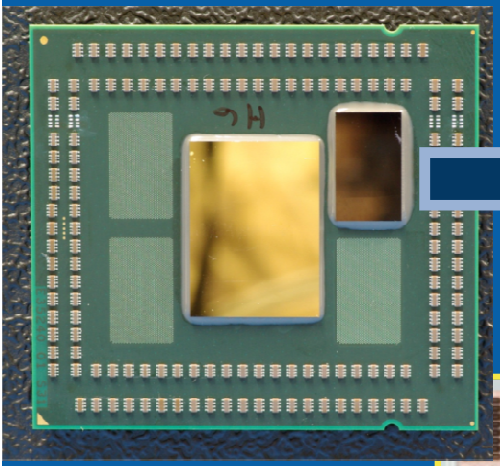


Integrated VR Technology - architecture

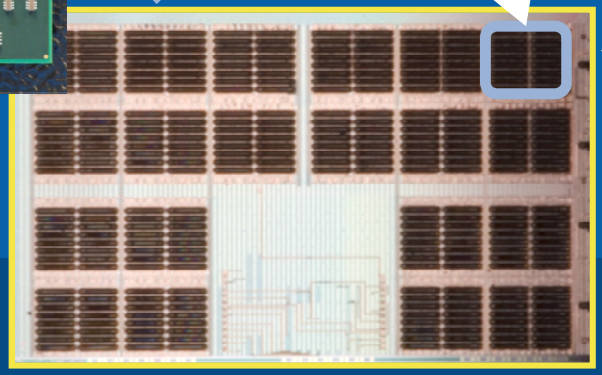
- 'Common Cell' Architecture – 20 cells
- Architecture supports flat efficiency curve
- Fine grain power management
  - Allows for multiple voltage rails
- Telemetry and Margining features
- Active Voltage Positioning for current sharing and balance
- Control features, including: JTAG, FPGA, Test/BIST



General Arch

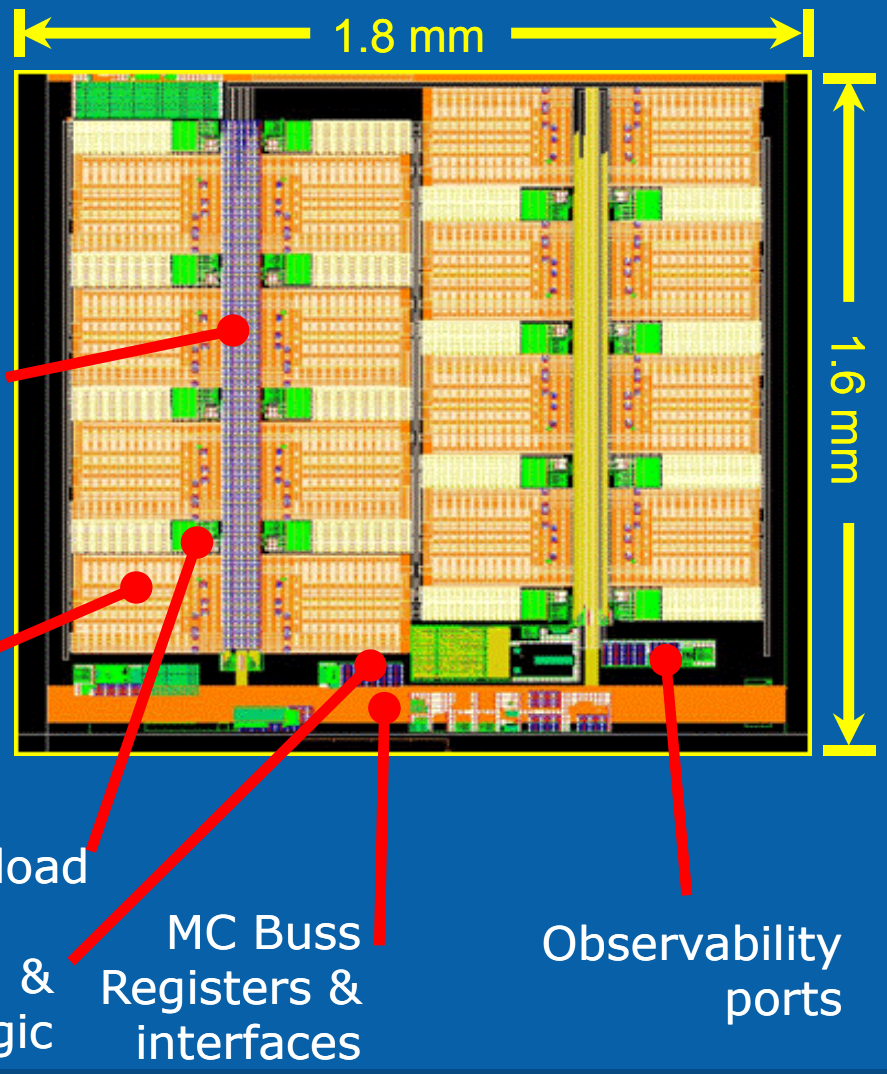


Power cell
- 2.8 mm²



Power Cell Architecture

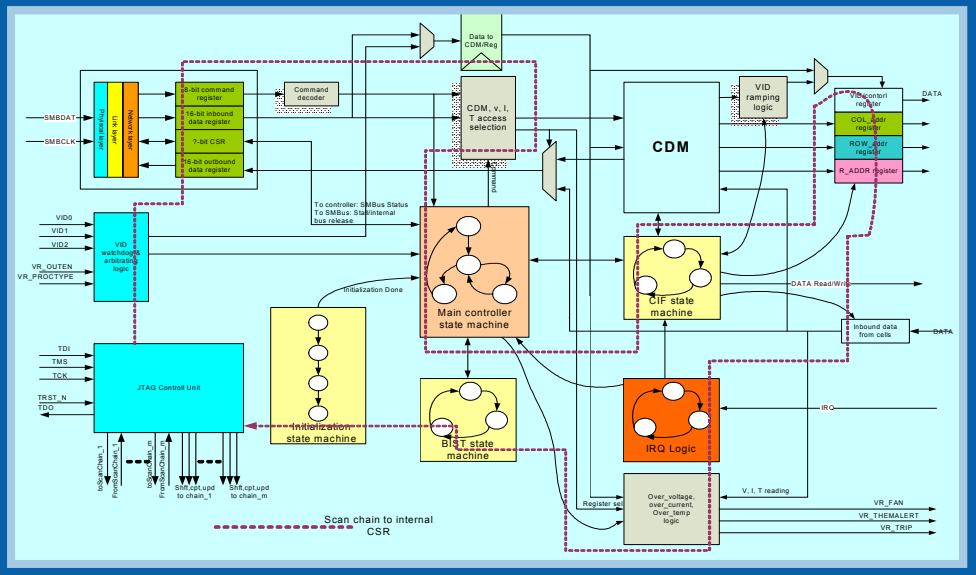
- Each Power cell == Mini VR
  - Up to 25A rating* - tested
  - Programmable switching frequency 30MHz to 140MHz
  - Ring coupled inductor topology
- 16 phases per power cell, 320 phases per chip
  - High phase count reduces noise, ripple
  - High granularity
  - Cell shedding
  - Bridge shedding
- BIST
  - Self-load and characterization system.



* Thermally constrained

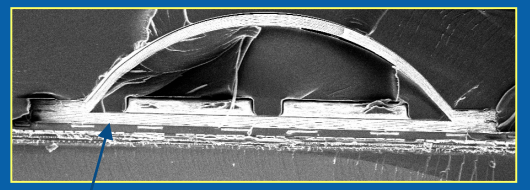
Master Control Architecture

- Master Controller Custom RTL
- VID controller
- JTAG 1194 compliant
- Cell Domain Map (V,T,I)
- AVP adjust
- Test & BIST per cell
- Softstart & Warmstart Algorithms
- Internal Buss interface logic
- IRQ buss
- Platform Interface support
  - Parallel buss
- Cell I-balance



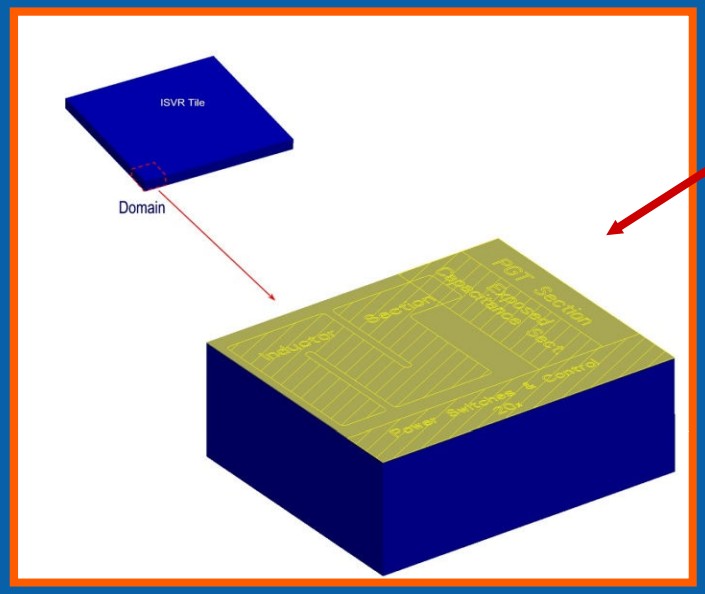
Master Controller Block

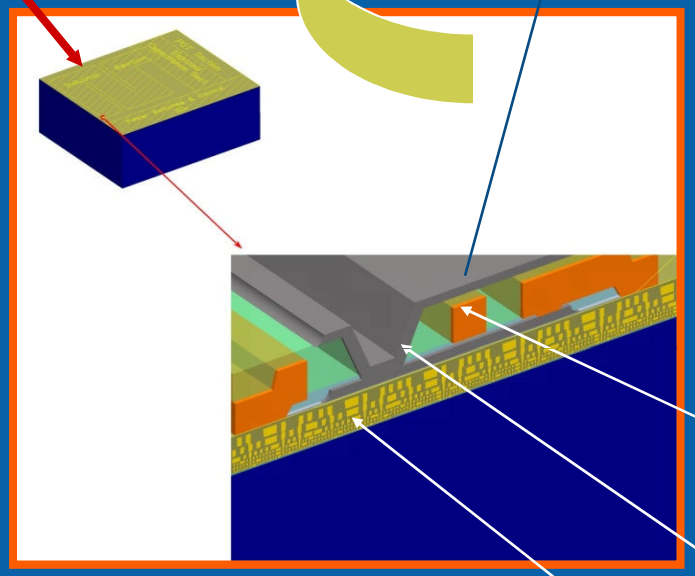
Thin-Film On-die Magnetics



Magnetic Cross section

Domain





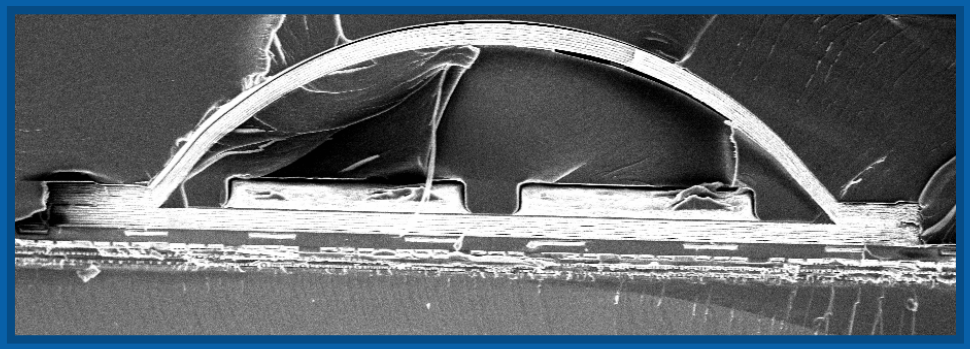
L metal

$Ni_{80}Fe_{20}$

m1-mX

- Technology targets & Stackup
- 90 nm technology for test devices
- 7-8 metal layers + thick metal(C4) + 2 Magnetic layers
- M1-m4/5 routing – bridge connections – decoupling capacitors
- M8 – inductor/transformer interconnect – ~10 um thick metal
- M7,M9 –magnetic material layers– ~4 um thick (laminated) $Ni_{80}Fe_{20}$

Gains from on-die magnetics



Magnetic SEM Cross section

- Energy density increased
- Volume shrinks
- Power Loss decreased

$$W_M = \frac{1}{2}\iiint_{\upsilon} \vec{B}\cdot\vec{H}d\upsilon \cong \frac{B^2\upsilon}{2\mu_r\mu_0}$$

$$\frac{W_M}{W_A} \cong \mu_r$$

$$W_a \cong W_m \Rightarrow \upsilon_m\mu_r \cong \upsilon_a$$

$$\frac{R_a}{R_m} = \frac{P_a}{P_m} \approx \frac{l_m\sqrt{\mu_r}}{l_a}$$

Energy density in thin film magnetics volume compared with air core inductor is proportional to permeability μ_r which is typically > 1000

Thin-Film Magnetics in relation to VR Ckts

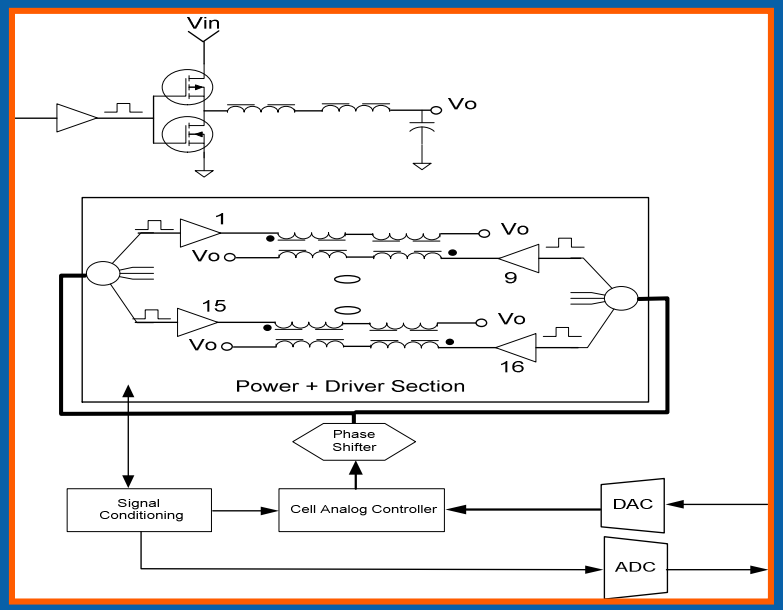
- L_{self} ~ 17nH per phase. - K~93%
- 16 phase – 25A/cell Imax
- 2.8 mm² per cell

$$P_{L\_c} \cong \Delta I^2 R_c = \frac{\Delta I^2 l_c}{\sigma w_c t_c}$$

$$L \cong \frac{\Delta V \Delta T}{\Delta I} = \frac{\Delta V (1/F) D}{\Delta I}$$

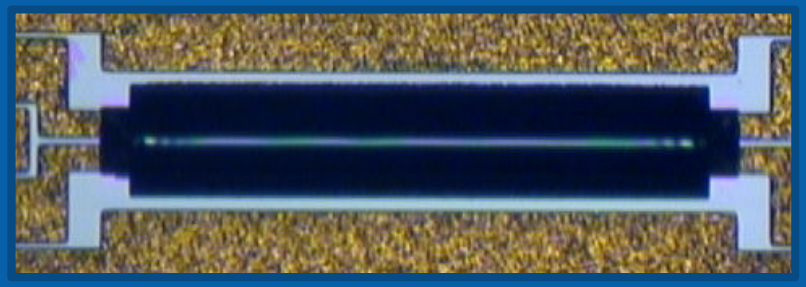
$$* L_{die} \cong \frac{\Delta V (1/F) D}{\Delta I} \cong \frac{B_{Sat} w t_m}{\Delta I}$$

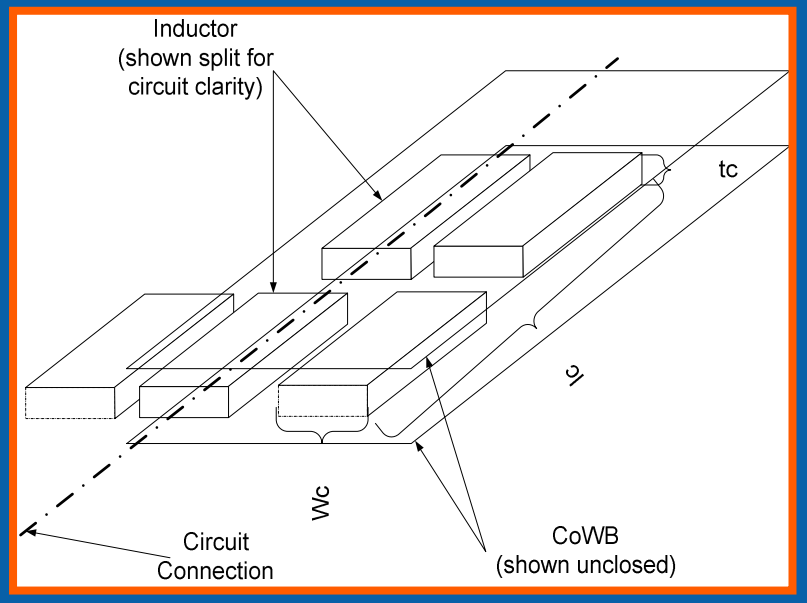
Cell Circuit



Inductor Physical

Single Magnetic Top View

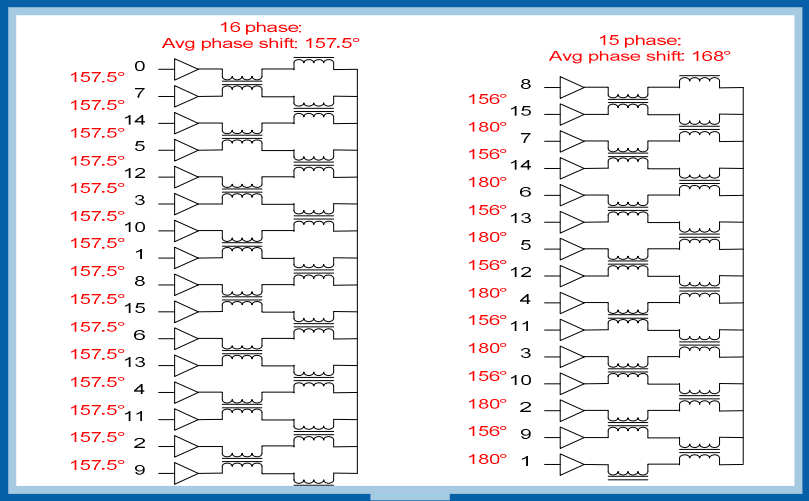


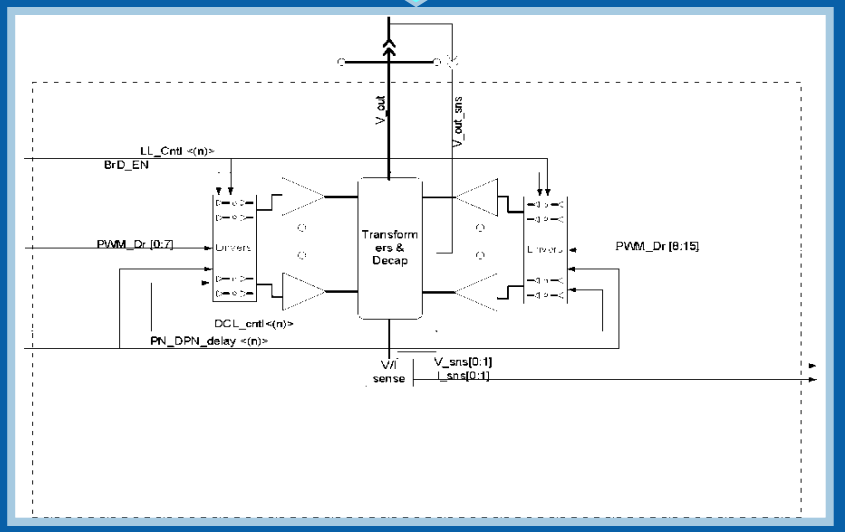


Power Train Architecture

- Cell level power train & Local Controller
- 16 phase 60-140 Mhz (per phase) coupled inductor
- Controller – type I analog
- Current Sense
- Flat efficiency with bridge shedding
- Loop programmable
- Register control between master controller and local cell controller
- Monitor and Observability thru pass-gate port design

16 phase VR

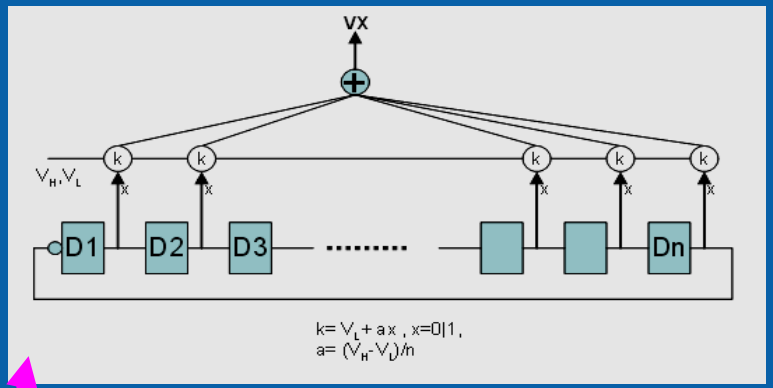




Power Cell Power Train Drive Block

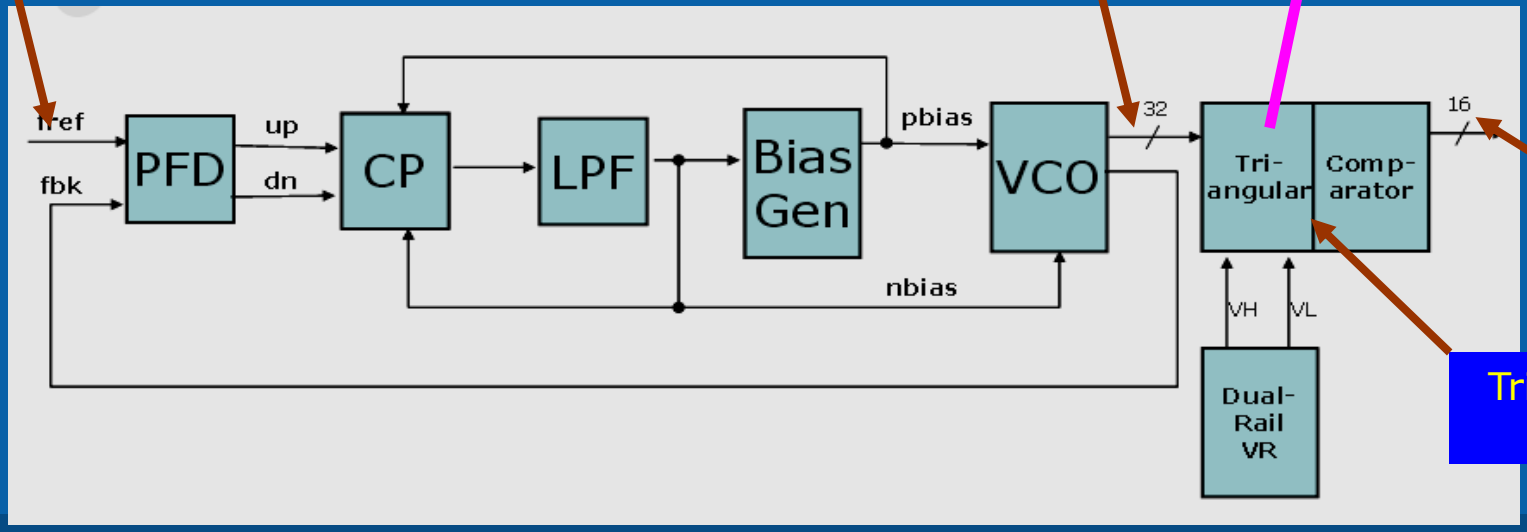
PWM topology

- Differential low power self-biased PLL
- Pulse width control by:
  - Clock => Triangle wave => pulses with variable duty cycle



Ref Clock
1 phase
50% duty

Clock
16 phases
50% duty

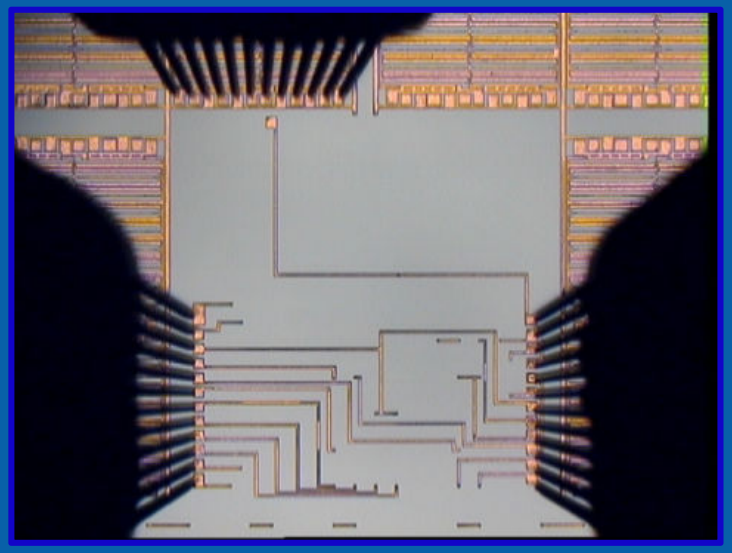


Pulses
16 phases
Variable duty

Triangle Wave
16 phases

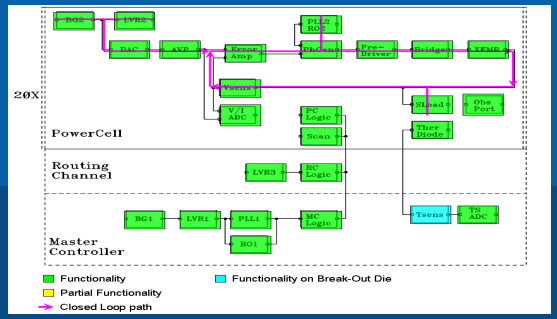
Some Practical Silicon VR Design Considerations…

- Ring-coupled vs. other topologies
  - Ring-coupled allows for current balance between all phases which can reduce phase imbalances leading to higher loss.
  - Negatives are there is a 22.5 degree imbalance intrinsic in the next adjacent pair.
- C4 alignment is crucial in layout – between the inductors…
- Ripple current control and saturation mitigation
  - Input ripple crucial as much as output – de-intranement
- PLL placement – local vs. global
- Observability analog/digital
- Multiple stage bridge arrangement
- Noise mitigation circuitry – RR's must be set up front between adjacent circuits



Test Results: Snap-shot of circuits – both Wafer Probe & Package

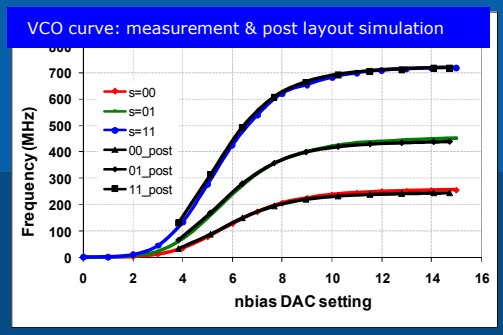
- Bandgap
- All internal linear regulators (LDO's)
- Sensors
  - V/I sensors & ADC used for known-good-die screening –all were functional (not fully debugged though)
  - Temperature sensor and its ADC functional on break-out die



- Interface logic
  - Enabled full programming through either parallel bus or scan
- DFT features
  - such as manual programming of VCO frequency
- Observability ports
  - To look at pre-determined internal nodes

AVP

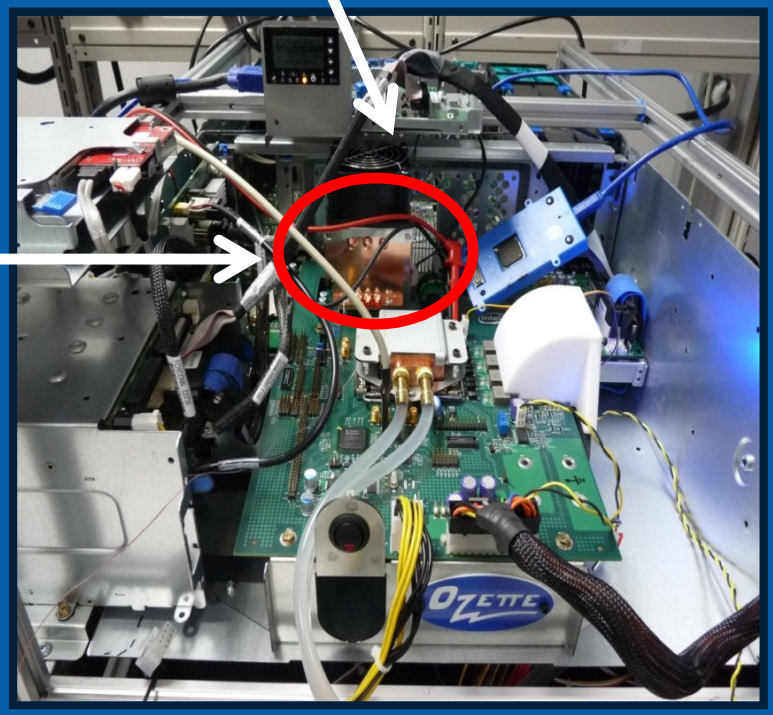
- Shared all 20 Cells

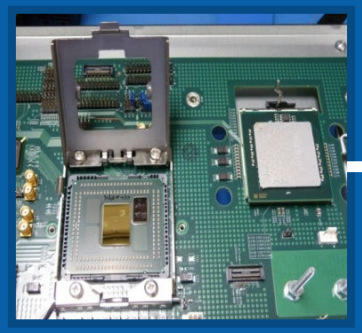


Booted 90W Server CPU – only 3 cells!

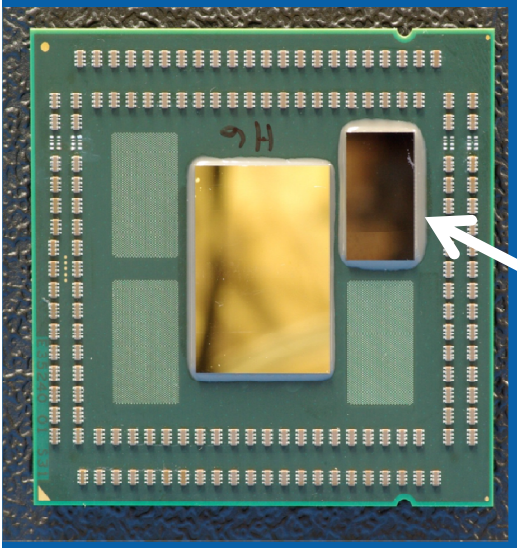
- With 40% of Output Filter Cap*
- Continuous operation with virus for 4+hours
  - No Errors

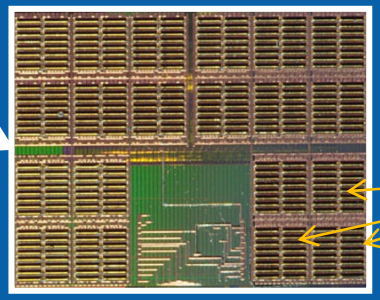
Intel® Xeon® Processor E7330



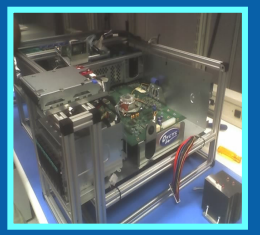


ISVR





These 3 cells!

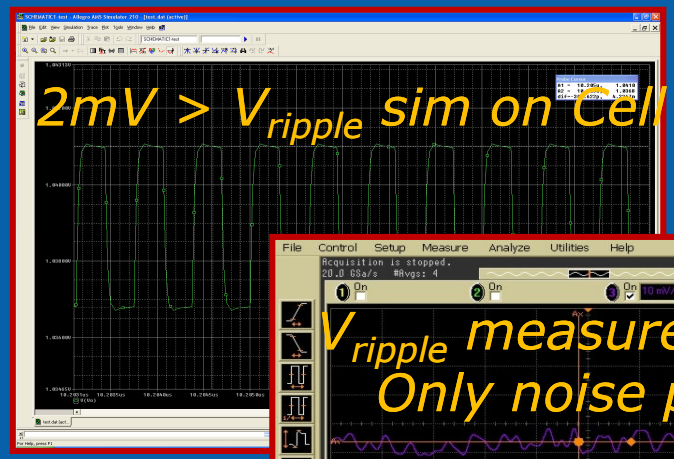


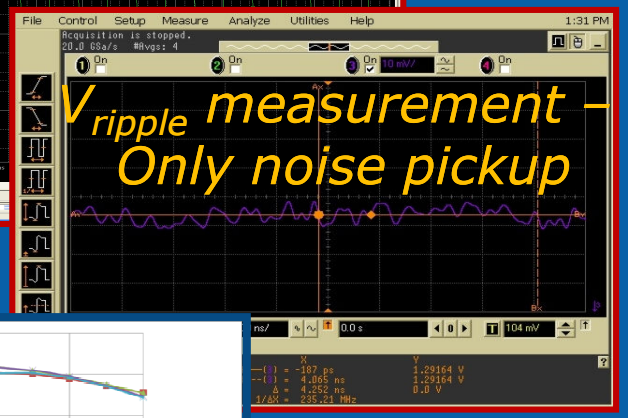
*Compared with MBVR

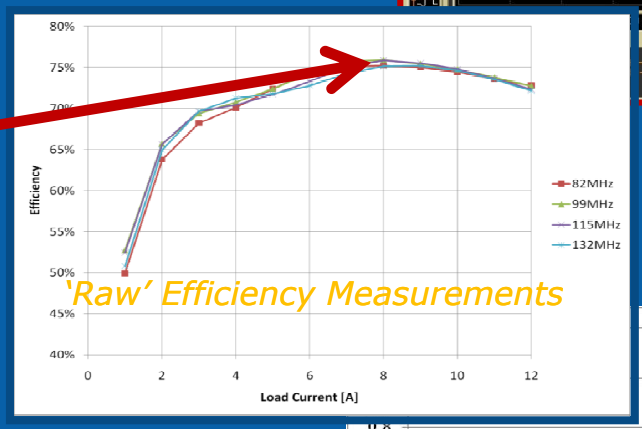
V_{ripple} & V_{TT} & *Efficiency*

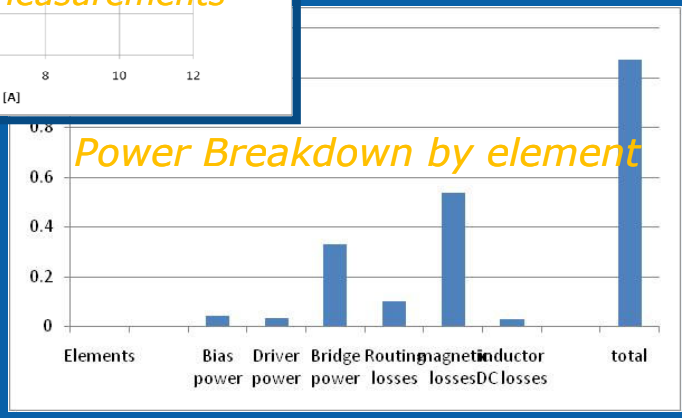
- Voltage Ripple V_{ripple}
- Measurements in lab on ISVR indicate ripple is almost non-existent
- Simulations yielded worst case *+/-2mv*
- V_{TT} Thermal drift
- Most error is calibrated out and leftover is linearized over temperature range to less than *1mV*
- Basic Test (no changes) ~76% peak
  - Bias circuits all on.
- Efficiency* ~***82%*** *speculated* with basic changes for 'product' level intro
  - Inductor topology coupling change
  - Non-lab level magnetics processed
  - Bias pwr re-distributed
  - Driver/Bridge circuits re-biased
  - Non-test bridge/output routing

*Does not include additional advancements that cannot be reported at this time.









Summary on ISVR…

- 400A capable – tested to 220A for less than ½ of chip – both sides alternated!
  - Board thermally limited.
- Booted and ran server processor (90W design) with 2 cells – ran with 3 cells under Linpack™ for 4+ hours.
- Ripple below noise threshold.
- Efficiency in low 80's with minor changes
  - Additional changes possible will boost up.*
- Density is ~8A/mm^2 thermally constrained.

Last Message: Power Delivery and Power Management Must be Combined

- Integrated Magnetics is a key enabler which can alter the way we deliver power to silicon
- *The Key*: Combining certain circuits, architecture and IM can lead to a revolutionary solution that is highly compelling
- SoC's for CE's are clearly a synergistic area which is hungry for such a technology – this is because technology scales…
- Questions?